

CDMS24760-120

**SILICON CARBIDE
N-CHANNEL MOSFET**



TO-247 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CDMS24760-120 is an N-channel silicon carbide MOSFET designed for high speed switching and fast reverse recovery applications.

MARKING: CDMS247

60-120

MAXIMUM RATINGS: ($T_J=25^\circ\text{C}$)

Drain-Source Voltage
Gate-Source Voltage
Continuous Drain Current
Pulsed Drain Current
Operating and Storage Junction Temperature
Power Dissipation

SYMBOL

SYMBOL		UNITS
V_{DS}	1200	V
V_{GS}	20	V
I_D	21	A
I_{DM}	35	A
T_J, T_{stg}	-55 to +175	$^\circ\text{C}$
P_D	28	W

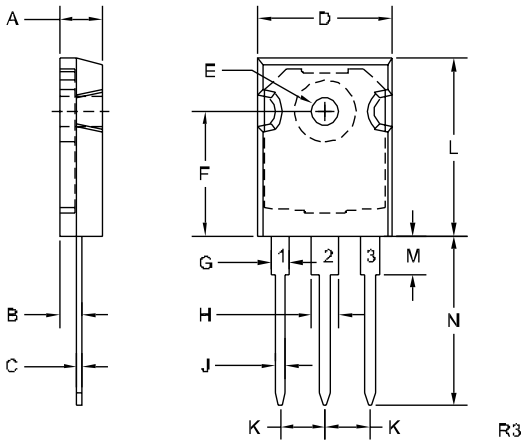
ELECTRICAL CHARACTERISTICS: ($T_J=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{DSS}	$V_{DS}=1200\text{V}, V_{GS}=0\text{V}$		50		nA
I_{GSS}	$V_{GS}=15\text{V}$		30		pA
$r_{DS(ON)}$	$V_{GS}=15\text{V}, I_D=10\text{A}$		60		m Ω
G_m	$V_{DS}=10\text{V}, I_D=10\text{A}$		7.0		S
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=17.5\text{mA}$		2.6		V
R_G	$f=1\text{MHz}$		10		Ω
C_{iss}	$V_{DS}=1000\text{V}, V_{GS}=0, f=1.0\text{MHz}$		0.9		nF
C_{oss}	$V_{DS}=1000\text{V}, V_{GS}=0, f=1.0\text{MHz}$		50		pF
C_{rss}	$V_{DS}=1000\text{V}, V_{GS}=0, f=1.0\text{MHz}$		8		pF
E_{oss}	$V_{DS}=800\text{V}, V_{GS}=15\text{V}, I_D=20\text{A}$		40		μJ
E_{on}	$V_{DS}=800\text{V}, V_{GS}=15\text{V}, I_D=20\text{A}$		600		μJ
E_{off}	$V_{DS}=800\text{V}, V_{GS}=15\text{V}, I_D=20\text{A}$		100		μJ
t_r	$V_{DS}=800\text{V}, V_{GS}=15\text{V}, I_D=20\text{A}$		18		ns
t_f	$V_{DS}=800\text{V}, V_{GS}=15\text{V}, I_D=20\text{A}$		16		ns
$t_{d(on)}$	$V_{DS}=800\text{V}, V_{GS}=15\text{V}, I_D=20\text{A}$		45		ns
$t_{d(off)}$	$V_{DS}=800\text{V}, V_{GS}=15\text{V}, I_D=20\text{A}$		35		ns
V_{SD}	$V_{GS}=0\text{V}, I_S=5.0\text{A}$			5.0	V

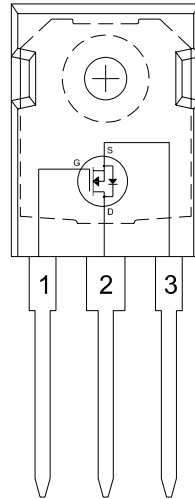
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TO-247 CASE - MECHANICAL OUTLINE



R3



LEAD CODE:

- 1) Gate
- 2) Drain
- 3) Source

MARKING:

CDMS247

60-120

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.184	0.211	4.68	5.36
B	0.087	0.110	2.20	2.80
C	0.019	0.028	0.48	0.70
D	0.606	0.638	15.38	16.20
E (DIA)	0.128	0.144	3.25	3.65
F	0.583	0.607	14.81	15.42
G	0.072	0.097	1.82	2.46
H	0.115	0.127	2.92	3.23
J	0.035	0.060	0.89	1.53
K	0.207	0.223	5.26	5.66
L	0.812	0.881	20.63	22.38
M	0.145	0.177	3.68	4.50
N	0.728	0.846	18.50	21.50

TO-247 (REV: R3)

R1 (30-July 2024)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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